

2P4M		
	单向可控硅 THYRISTOR	版本号 201603-A

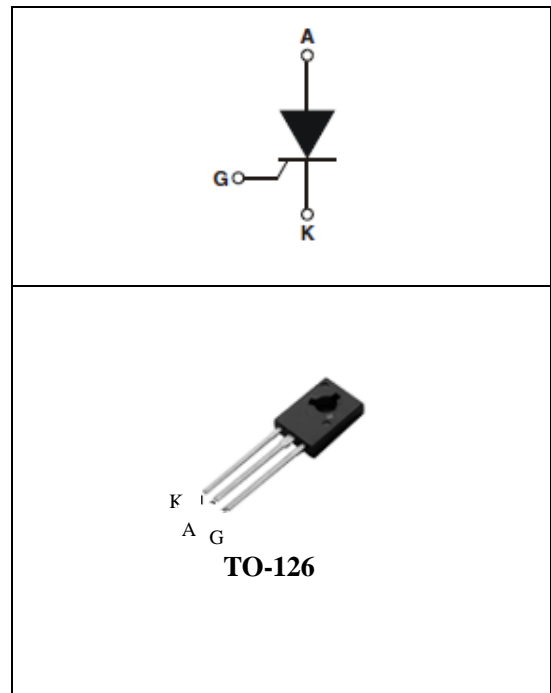
产品概述 GENERAL DESCRIPTION

2P4M 单向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术，dv/dt高，可靠性高，适用于控温、调光、马达控制。

2P4M Thyristor is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

主要参数 MAIN CHARACTERISTICS

参数 Parameter	数值 Value	单位 Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	600&800	V
I_{GT}	200	μA



产品特性 FEATURES

- | | |
|------------|------------------------|
| ● dv/dt高 | ● Highly dv/dt |
| ● 通态压降低 | ● Low on-state voltage |
| ● Rohs环保产品 | ● Rohs Products |

应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。

domestic lighting ,heating and motor speed controllers.

极限值(除非另有规定, T_j=25℃) ABSOLUTE RATINGS

 (T_j=25℃, unless otherwise specified)

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
I _{T(RMS)}	RMS 通态电流 RMS on-state current (full sine wave)	T _{lead} ≤51℃	4 A
I _{TSM}	通态峰值浪涌电流 Non repetitive surge peak on-state current	F=50Hz, t=20ms	20 A
I ² t	I ² t 耗散值 I ² t value for fusing	T _p =10ms	6 A ² s
di/dt	通态电流上升值 Critical rate of rise of on-state current	F=120Hz, T _j =125℃	50 A/μs
I _{GM}	门极峰值电流 Peak gate current	T _p =20μs, T _j =125℃	1.0 A
P _{G(AV)}	平均门极耗散功率 Average gate power dissipation	T _j =125℃	0.3 W
T _{stg}	贮存结温范围 Storage junction temperature range		-40+150 ℃
T _j	工作结温范围 Operating junction temperature range		-40+110 ℃

电参数(除非另有规定, T_j=25℃) ELECTRICAL CHARACTERISTICS

 (T_j=25℃, unless otherwise specified)

参数 Parameter	符号 Symbol	规范值 Value	单位 Unit	测试条件 Test Conditions
触发电流 Gate trigger current	I _{GT}	≤200	μA	V _D =6V, I _T =0.01A
触发电压 Gate trigger voltage	V _{GT}	≤1.0	V	V _D =7V, I _T =0.01A
维持电流 Holding current	I _H	≤5	mA	V _D =7V, I _T =0.01A
擎住电流 Latching current	I _L	≤8	mA	V _D =7V, I _T =0.01A
电压上升率 Rise of off-state voltage	dv/dt	≥15	V/μS	V _D =67% V _{DRM}
通态压降 Peak on-state voltage	V _{TM}	≤1.6	V	I _T =5A
断态漏电流 Peak repetitive forward blocking current	I _{DRM}	≤10	μA	V _{RRM} =V _{DRM} , T _j =25℃
	I _{RRM}	≤2	mA	V _{RRM} =V _{DRM} , T _j =125℃

热特性 THERMAL RESISTANCES

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
R _{th(j-c)}	Junction to case(AC)	4.1	℃/W
R _{th(j-a)}	Junction to ambient	100	℃/W

特征曲线 ELECTRICAL CHARACTERISTICS (CURVES)

图1 最大耗散功率与RMS通态电流关系
Fig.1.Maximum Power Dissipation Versus on-state current

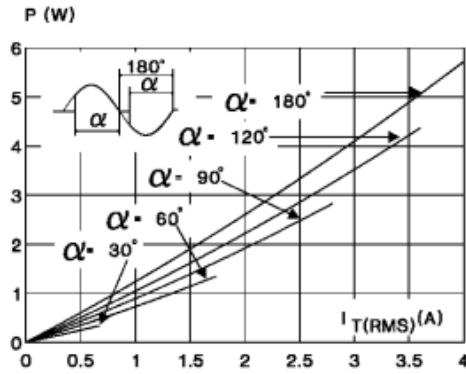


图3 通态特性
Fig.3.On-State Characteristics

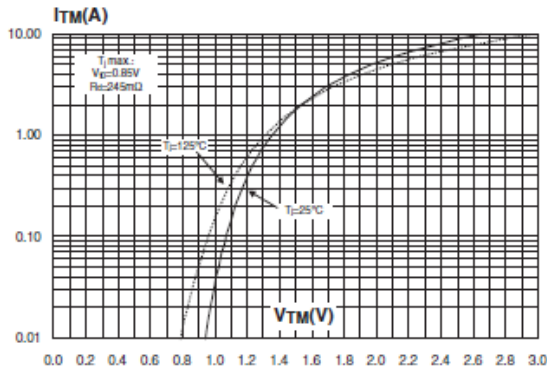


图5 IGT、IH、IL相对值（相对于25°C）与结温关系

Fig.5.Relative Variation Of Gate Trigger Current, Holding Current And Latching Current Versus Junction Temperature (Typical Value)

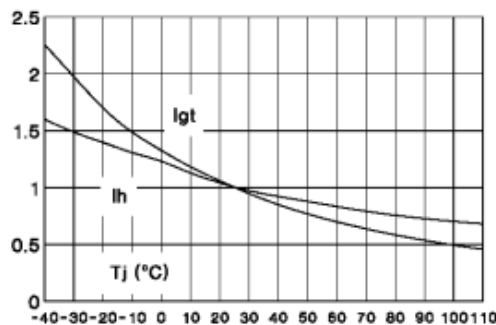


图2 RMS通态电流与Tc温度关系
Fig.2. IT(RMS) On-state Current Versus TL

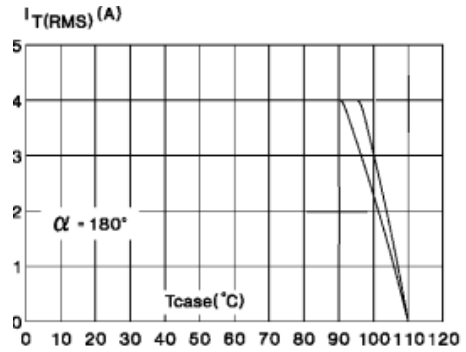
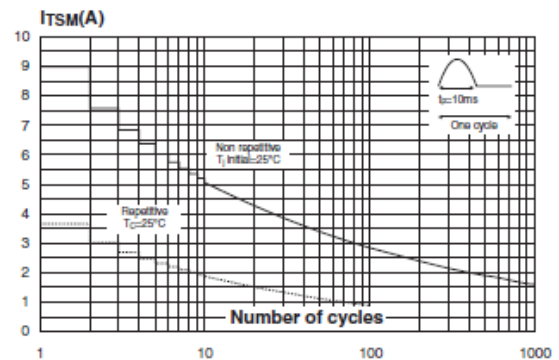
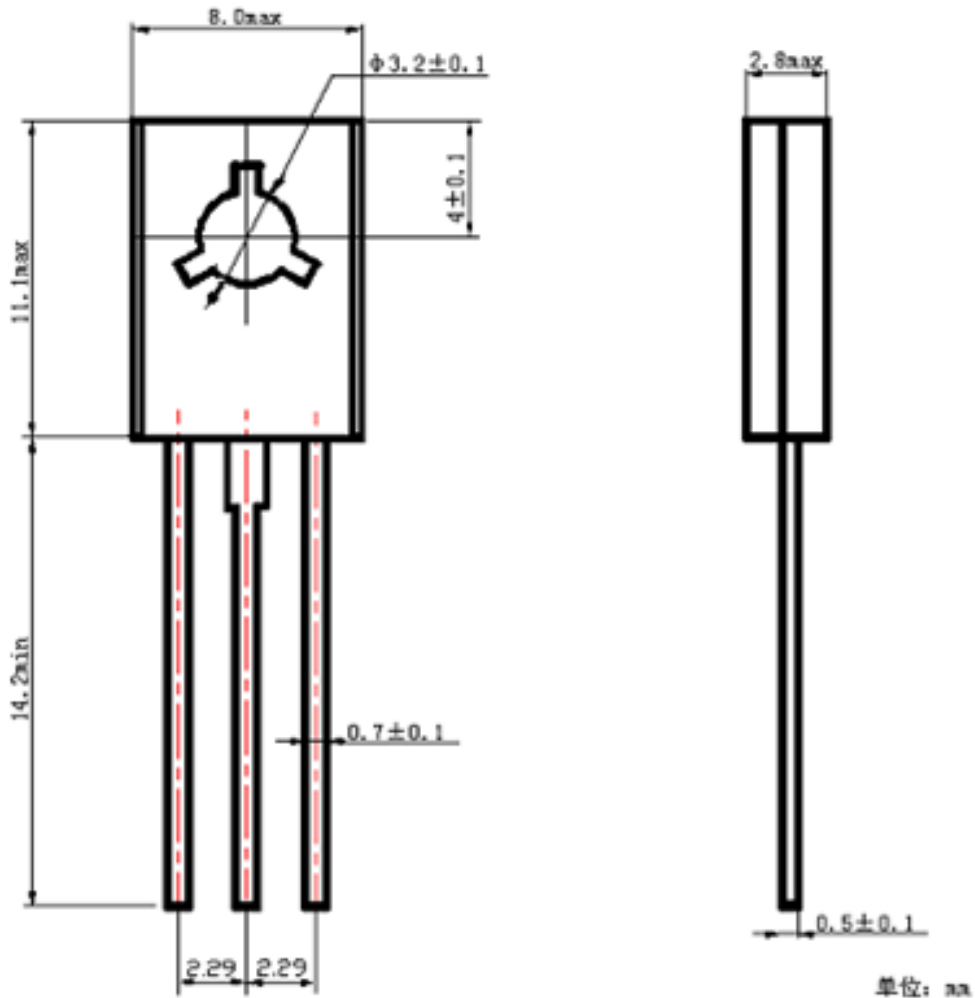


图4 通态浪涌峰值电流与周期数关系
Fig.4.Surge Peak On-state Current Versus Number Cycles



封装尺寸 PACKAGE MECHANICAL DATA

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